MSKSEMI 美森科







TVS



TSS



MOV



GDT



PIFF

T2N7002AK-MS

Product specification





Features

- 60V,0.3A, RDS(ON) =2.2Ω@VGS=10V
- Improved dv/dt capability
- Fast switching
- Green Device Available
- G-S ESD Protection Diode Embedded
- ESD protected up to 2KV

BVDSS	RDSON	ID
60V	2.2Ω	0.3A

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking
SOT-23	G	72K

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
Vos	Drain- Source Voltage	60	V
Vgs	Gate- Sou₁ce Voltage	±20	V
I _D	Drain Current – Continuous (T _C =25℃)	0.3	А
July 10	Drain Current – Continuous (T _C =100∘c)		А
Ідм	Drain Current – Pulsed ¹	0.8	А
Pp	Power Dissipation (T _C =25 ℃)	0.35	W
Power Dissipation – Derate above 25 ℃		0.003	W/°C
Тѕтс	Storage Temperature Range	-50 to 150	°C
TJ	Operating Junction Temperature Range	-50 to 150	°C



Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		357	°C/W

Electrical Characteristics(TJ=25 °C , unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain- Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
1	Drain- Source Leakage Current	V _{DS} =60V , V _{GS} =0V , T _J =25℃			1	ŭΑ
IDSS	1	V _{DS} =48V , V _{GS} =0V , T _J =125℃			10	uА
Igss	Gate- Source Leakage Current	V _{GS} ±20V , V _{DS} =0V			±10	uА

On Characteristics

D	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =0.3A		2.2	2.8	Ω
Rds(on)	Static Drain- Source On- Nesistance	V _{GS} =4.5V , I _D =0.2A		2 4	3 0	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250uA$	1	1.6	2.5	V
gfs	Forward Transconductance	V _{DS} =10V , I _D =0.3A		0.5		S

Dynamic and switching Characteristics

<i>- y</i>		•			
Qg	Total Gate Charge ^{2, 3}		 3.7	5.6	
Qgs	Gate-Source Charge ^{2, 3}	V_{DS} =30V , V_{GS} =10V , I_{D} =1A	 0.9	1.4	nC
Qgd	Gate-Drain Charge ² , ³		 0.4	0.6	
T _{d(on)}	Turn-On Delay Time ^{2, 3}		 3	6	
Tr	Rise Time ^{2, 3}	V_{DD} =30V , V_{GS} =10V , R_{G} =6 Ω	 5	10	ns
T _{d(off)}	Turn-Off Delay Time ^{2, 3}	I _D =0.2A	 14	27	115
Tf	Fall Time ^{2 , 3}		 9	17	
Ciss	Input Capacitance		 25.5	38	
Coss	Output Capacitance	V_{DS} =30V , V_{GS} =0V , F=1MHz	 17	26	pF
Crss	Reverse Transfer Capacitance		 7.8	12	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V _G =V _D =0V , Force Current			0.3	Α
lsм	Pulsed Source Current	VG-VD-0V, Force Current			1.2	Α
VsD	Diode Forward Voltage	V _{GS} =0V , I _S =1A , T _J =25℃			1.2	٧
trr	Reverse Recovery Time	V _{GS} =50V, I _S =1A , dI/dt=100A/μs		3.4		ns
Qrr	Reverse Recovery Charge	T _J =25℃		0.7		nC

Note:

- 1.Repetitive Rating: Pulsed width limited by maximum junction temperature.
- $2\,.$ The data tested by pulsed , pulse width $\leqq 300\,us$, duty cycle $\leqq 2\,\%\,.$
- 3. Essentially independent of operating temperature.

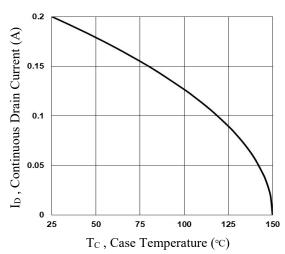


Fig.1 Continuous Drain Current vs. Tc

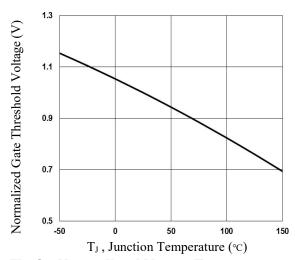


Fig.3 Normalized V_{th} vs. T_J

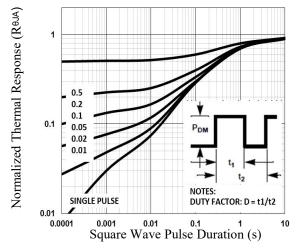


Fig.5 Normalized Transient Impedance

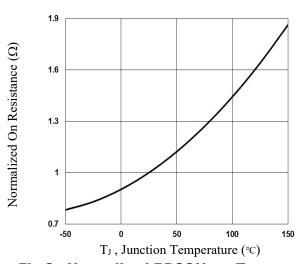


Fig.2 Normalized RDSON vs. T_J

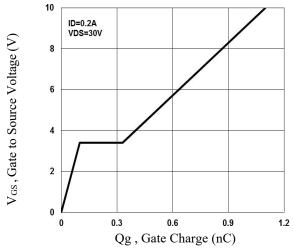


Fig.4 Gate Charge Waveform

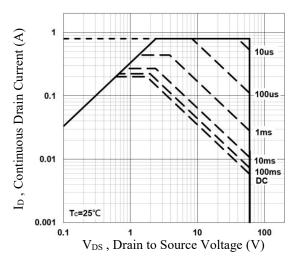
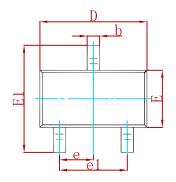
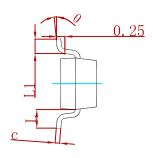


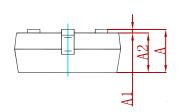
Fig.6 Maximum Safe Operation Area



PACKAGE MECHANICAL DATA

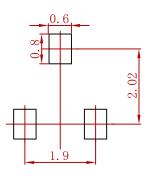






0	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950) TYP	0.037	7 TYP
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022	REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
T2N7002AK-MS	SOT-23	3000



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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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